Product data sheet

1. General description

Hyperfast power diode in a SOD59 (2-lead TO-220AC) plastic package.

2. Features and benefits

- Fast switching
- Low leakage current
- · Low reverse recovery current
- Low thermal resistance
- · Reduces switching losses in associated MOSFET or IGBT

3. Applications

- Active PFC in air conditioner
- High frequency switched-mode power supplies
- Continuous Current Mode (CCM) Power Factor Correction (PFC)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage		600			V	
$I_{F(AV)}$	average forward current	δ = 0.5; $T_{mb} \le$ 121 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	15		А		
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{mb} ≤ 121 °C; square-wave pulse	30		Α		
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4			Α		
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse			Α		
Symbol	Parameter	Conditions	Min Typ Max		Max	Unit	
Static ch	aracteristics			,			
V_{F}	forward voltage	I _F = 15 A; T _j = 150 °C; <u>Fig. 6</u>	- 1.4 2		2	V	
Dynamic	characteristics				•	•	
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 200 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7		-	13	18	ns

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BYC15-600P

Hyperfast power diode

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode	mb	
2	Α	anode	7 0 1	K — A 001aaa020
mb	mb	mounting base; connected to cathode	1 2 TO-220AC (SOD59)	001aaa020

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BYC15-600P	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59		

7. Marking

Table 4. Marking codes

Type number	Marking codes
BYC15-600P	BYC15-600P

Hyperfast power diode

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		600	V
V_{RWM}	crest working reverse voltage		600	V
V_R	reverse voltage	DC	600	V
$I_{F(AV)}$	average forward current	$δ = 0.5$; $T_{mb} \le 121$ °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	15	А
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 μs; T _{mb} ≤ 121 °C; square-wave pulse	30	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	180	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	200	А
T _{stg}	storage temperature		-65 to 175	°C
T _j	junction temperature		175	°C

Hyperfast power diode

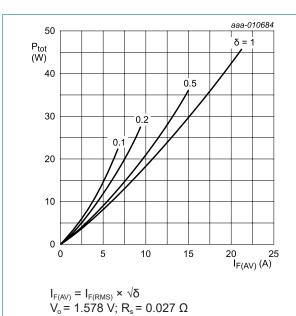


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

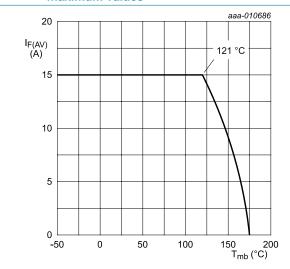
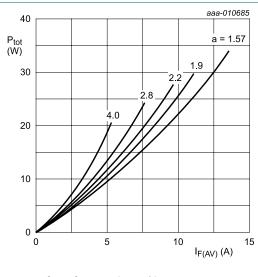


Fig. 3. Forward current as a function of mounting base temperature; maximum values



a = form factor = $I_{F(RMS)}/I_{F(AV)}$ $V_o = 1.578 \text{ V}; R_s = 0.027 \Omega$

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

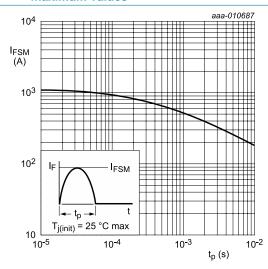


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

Hyperfast power diode

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	with heatsink compound; Fig. 5	-	-	1.5	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

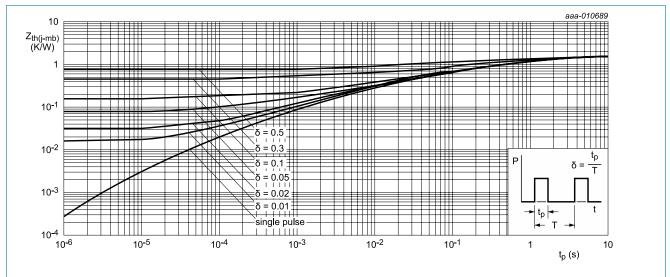
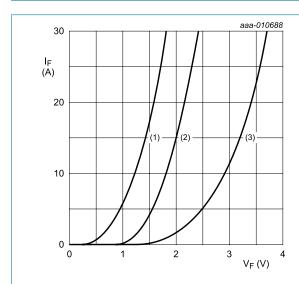


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics		'			
V _F fo	forward voltage	I _F = 15 A; T _j = 25 °C; <u>Fig. 6</u>	-	2.7	3.2	V
		I _F = 15 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.4	2	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	10	μA
		V _R = 600 V; T _j = 150 °C	-	-	1	mA
Dynamic	characteristics					
Q _r	recovered charge	I _F = 15 A; V _R = 200 V; dI _F /dt = 200 A/ μs; T _J = 25 °C; <u>Fig. 7</u>	-	30	-	nC
		$I_F = 15 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 125 ^{\circ}\text{C}; Fig. 7$	-	115	-	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	13	18	ns
		$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	22	-	ns
		$I_F = 15 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	28	-	ns
		$I_F = 15 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	39	-	ns
I _{RM}	peak reverse recovery current	$I_F = 15 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	2.1	-	А
		$I_F = 15 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_i = 125 \text{ °C}; \frac{\text{Fig. 7}}{\text{C}}$	-	5.8	-	А



(1) T_i = 150 °C; typical values

(2) $T_j = 150$ °C; maximum values (3) $T_j = 25$ °C; maximum values

 $V_o = 1.578 \text{ V}; R_s = 0.027 \Omega$

Fig. 6. Forward current as a function of forward voltage

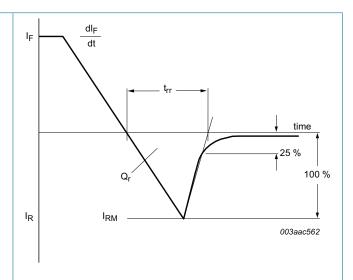
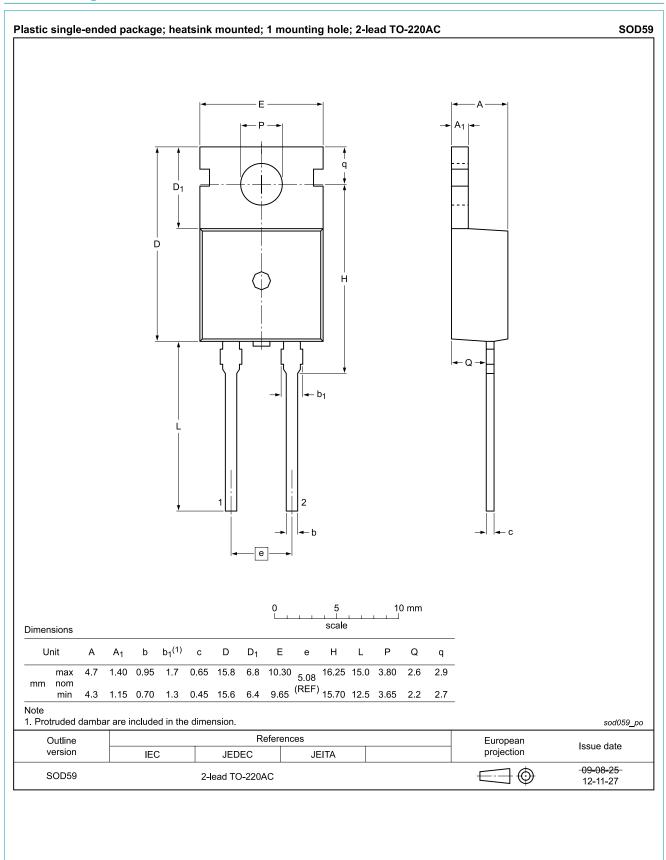


Fig. 7. Reverse recovery definitions; ramp recovery

11. Package outline



Hyperfast power diode

12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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